

MOS FIELD EFFECT TRANSISTOR

2SK3432

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3432 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Super low on-state resistance:
- ★ RDS(on)1 = $4.0 \text{ m}\Omega$ MAX. (Vgs = 10 V, ID = 42 A)
- \bigstar RDS(on)2 = 6.9 m Ω MAX. (VGS = 4 V, ID = 42 A)
 - Low Ciss: Ciss = 9500 pF TYP.
 - Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

	Drain to Source Voltage	VDSS	40	V
	Gate to Source Voltage	Vgss	±20	V
	Drain Current (DC)	I _{D(DC)}	±83	Α
	Drain Current (pulse) Note1	D(pulse)	±332	Α
	Total Power Dissipation (Tc = 25°C)	PT	100	W
	Total Power Dissipation (T _A = 25°C)	Рт	1.5	W
	Channel Temperature	T_ch	150	°C
	Storage Temperature	T_{stg}	-55 to +150	°C
*	Single Avalanche Current Note2	las	69	Α
*	Single Avalanche Energy Note2	Eas	476	mJ

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1 %

2. Starting T_{ch} = 25 °C, R_G = 25 Ω , V_{GS} = 20 V \rightarrow 0 V

PART NUMBER	PACKAGE		
2SK3432	TO-220AB		
2SK3432-S	TO-262		
2SK3432-Z	TO-220SMD		

ORDERING INFORMATION

(TO-220AB)



(TO-262)



(TO-220SMD)



THERMAL RESISTANCE

Channel to Case	Rth(ch-C)	1.25	°C/W
Channel to Ambient	Rth(ch-A)	83.3	°C/W

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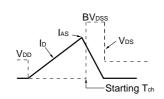


ELECTRICAL CHARACTERISTICS (TA = 25 °C)

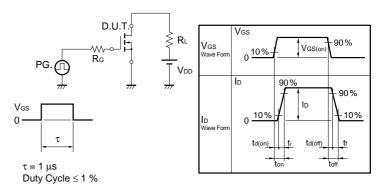
	CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
*	Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, ID = 42 A		3.2	4.0	mΩ
*		RDS(on)2	Vgs = 4 V, ID = 42 A		4.8	6.9	mΩ
	Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
*	Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 42 A	40	80		S
	Drain Leakage Current	Ioss	V _{DS} = 40 V, V _{GS} = 0 V			10	μΑ
	Gate to Source Leakage Current	Igss	Vgs = ±20 V, Vps = 0 V			±10	μΑ
	Input Capacitance	Ciss	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		9500		pF
	Output Capacitance	Coss			2200		pF
	Reverse Transfer Capacitance	Crss			920		pF
*	Turn-on Delay Time	td(on)	ID = 42 A, VGS(on) = 10 V, VDD = 20 V,		140		ns
*	Rise Time	tr	$R_G = 10 \Omega$		1800		ns
*	Turn-off Delay Time	td(off)			470		ns
*	Fall Time	t f			410		ns
*	Total Gate Charge	Q _G	ID = 83 A , VDD = 32 V, VGS = 10 V		150		nC
*	Gate to Source Charge	Qgs			29		nC
*	Gate to Drain Charge	Q _{GD}			45		nC
	Body Diode Forward Voltage	V _{F(S-D)}	IF = 83 A, VGS = 0 V		1.0		V
*	Reverse Recovery Time	trr	IF = 83 A, VGS = 0 V,		69		ns
*	Reverse Recovery Charge	Qrr	$di/dt = 100 A/\mu s$		130		nC

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c} \text{D.U.T.} \\ \text{Rg} = 25 \, \Omega \\ \text{VGS} = 20 \rightarrow 0 \, \text{V} \\ \end{array} \begin{array}{c} \text{PG.} \\ \text{W} \\ \text{W} \end{array} \begin{array}{c} \text{S} \\ \text{S} \\ \text{W} \end{array} \begin{array}{c} \text{O.U.T.} \\ \text{V} \\ \text{W} \end{array} \begin{array}{c} \text{V} \\ \text{W} \end{array}$



TEST CIRCUIT 2 SWITCHING TIME

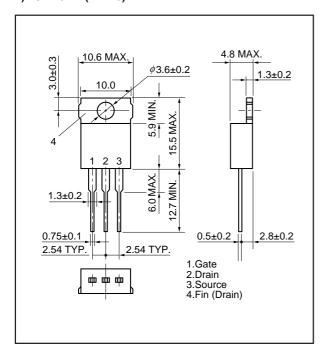


TEST CIRCUIT 3 GATE CHARGE

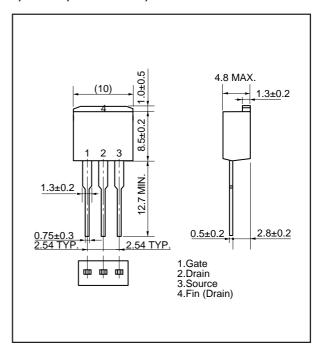


PACKAGE DRAWINGS (Unit: mm)

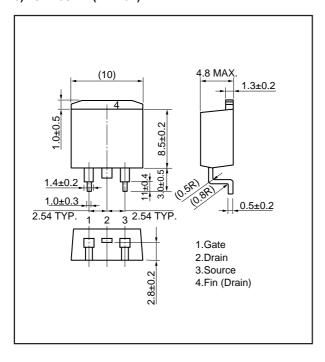
1) TO-220AB (MP-25)



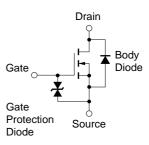
2) TO-262 (MP-25 Fin Cut)



3) TO-220SMD (MP-25Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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